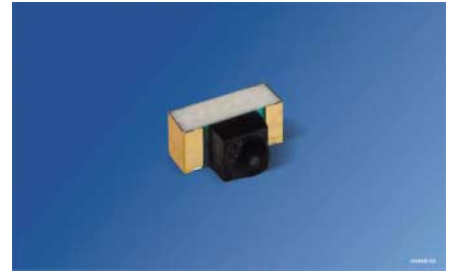


**Phototransistor**  
**Phototransistor**  
**Lead (Pb) Free Product - RoHS Compliant**

**SFH 3015 FA**



SFH 3015 FA

**Vorläufige Daten / Preliminary Data**

**Wesentliche Merkmale**

- Enger Empfangswinkel ( $\pm 13^\circ$ )
- Sidelooker mit geringer Bauhöhe (1,6 mm)
- Emitter im gleichen Gehäuse verfügbar:  
SFH 4015 und SFH 4045

**Anwendungen**

- Lichtschranken, Lichtvorhänge
- Sensorik
- Näherungssensor
- berührungsempfindliche Bildschirme

**Features**

- Narrow angle ( $\pm 13^\circ$ )
- Low profile sidelooker (1,6 mm)
- Emitter in same package available:  
SFH 4015 and SFH 4045

**Applications**

- Interrupters, Lightcurtains
- Sensors
- Proximity sensor
- Touchscreen

| Typ<br>Type | Bestellnummer<br>Ordering Code | Fotostrom , $E_e=0.1 \text{ mW/cm}^2, \lambda=950 \text{ nm}$ $V_{CE} = 5 \text{ V}$<br>Photocurrent<br>$I_{pce} (\mu\text{A})$ |
|-------------|--------------------------------|---------------------------------------------------------------------------------------------------------------------------------|
| SFH 3015 FA | Q65110A9730                    | 100...800                                                                                                                       |

**Grenzwerte**  
**Maximum Ratings**

| Bezeichnung<br>Parameter                                                  | Symbol<br>Symbol                         | Wert<br>Value | Einheit<br>Unit |
|---------------------------------------------------------------------------|------------------------------------------|---------------|-----------------|
| Betriebstemperatur<br>Operating temperature range                         | $T_{op}$                                 | - 25 ... + 85 | °C              |
| Lagertemperatur<br>Storage temperature range                              | $T_{stg}$                                | - 40 ... + 85 | °C              |
| Kollektor-Emitterspannung<br>Collector-emitter voltage                    | $V_{CE}$<br>$V_{CE} (t < 2 \text{ min})$ | 15<br>30      | V               |
| Kollektorstrom<br>Collector current                                       | $I_C$                                    | 15            | mA              |
| Kollektorspitzenstrom, $\tau < 10 \mu\text{s}$<br>Collector surge current | $I_{CS}$                                 | 75            | mA              |
| Emitter-Kollektorspannung<br>Emitter-collector voltage                    | $V_{EC}$                                 | 7             | V               |

**Kennwerte ( $T_A = 25 \text{ °C}$ )**  
**Characteristics**

| Bezeichnung<br>Parameter                                                                                                                                 | Symbol<br>Symbol             | Wert<br>Value      | Einheit<br>Unit |
|----------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------|--------------------|-----------------|
| Wellenlänge der max. Fotoempfindlichkeit<br>Wavelength of max. sensitivity                                                                               | $\lambda_{S \text{ max}}$    | 870                | nm              |
| Spektraler Bereich der Fotoempfindlichkeit<br>Spectral range of sensitivity, $S = 10\%$ of $S_{\text{max}}$                                              | $\lambda$                    | 770 ... 1090       | nm              |
| Bestrahlungsempfindliche Fläche<br>Radiant sensitive area                                                                                                | $A$                          | 0.04               | mm <sup>2</sup> |
| Abmessungen des Chips<br>Dimensions of chip                                                                                                              | $L \times B$<br>$L \times W$ | $0.35 \times 0.35$ | mm × mm         |
| Halbwinkel<br>Half angle                                                                                                                                 | $\varphi$                    | $\pm 13$           | Grad<br>deg.    |
| Kapazität, $V_{CE} = 5 \text{ V}$ , $f = 1 \text{ MHz}$ , $E = 0$<br>Capacitance                                                                         | $C_{CE}$                     | 1.3                | pF              |
| Dunkelstrom, $V_{CE} = 10 \text{ V}$ , $E = 0$<br>Dark current                                                                                           | $I_{CEO}$                    | 2 ( $\leq 50$ )    | nA              |
| Anstiegszeit/Abfallzeit, $\lambda = 950 \text{ nm}$ , $I_C = 1 \text{ mA}$ ,<br>$V_{CC} = 5 \text{ V}$ , $R_L = 1 \text{ k}\Omega$<br>Rise and fall time | $t_r$ , $t_f$                | 7                  | $\mu\text{s}$   |

Die Fototransistoren werden nach ihrer Fotoempfindlichkeit gruppiert und mit arabischen Ziffern gekennzeichnet.

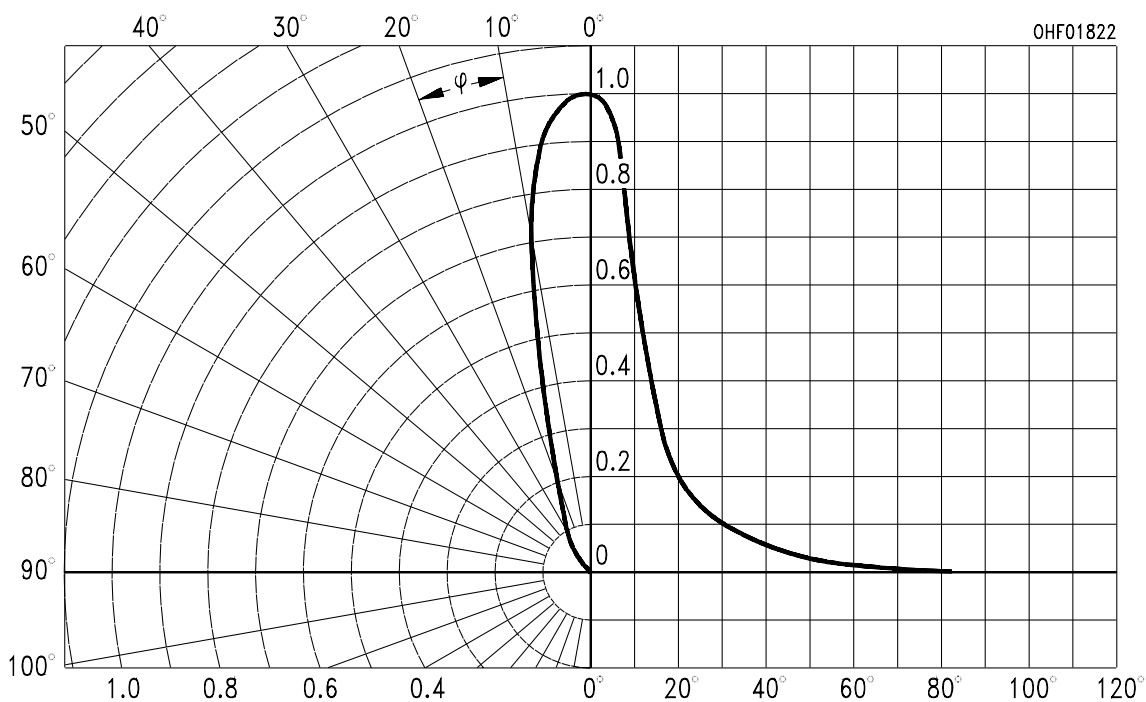
The phototransistors are grouped according to their spectral sensitivity and distinguished by arabian figures.

| Bezeichnung<br>Parameter                                                                                                                        | Symbol<br>Symbol | Wert<br>Value |             |             |             | Einheit<br>Unit |
|-------------------------------------------------------------------------------------------------------------------------------------------------|------------------|---------------|-------------|-------------|-------------|-----------------|
|                                                                                                                                                 |                  | -1            | -2          | -3          | -4          |                 |
| Fotostrom, $V_{CE} = 5\text{ V}$ , $\lambda = 950\text{ nm}$ ,<br>$E_e = 0.1\text{ mW/cm}^2$<br>Photocurrent                                    | $I_{PCE}$        | 100 ... 200   | 160 ... 320 | 250 ... 500 | 400 ... 800 | $\mu\text{A}$   |
| Kollektor-Emitter-Sättigungsspannung<br>Collector-emitter saturation voltage<br>$I_C = I_{PCEmin}^{1)} \times 0.3$ , $E_e = 0.1\text{ mW/cm}^2$ | $V_{CEsat}$      | 170           | 170         | 170         | 170         | mV              |

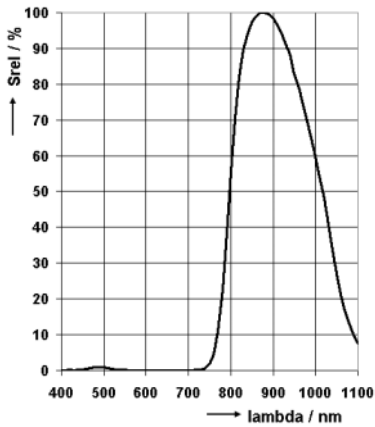
<sup>1)</sup>  $I_{PCEmin}$  ist der minimale Fotostrom der jeweiligen Gruppe.

<sup>1)</sup>  $I_{PCEmin}$  is the min. photocurrent of the specified group.

#### Directional Characteristics $S_{rel} = f(\varphi)$

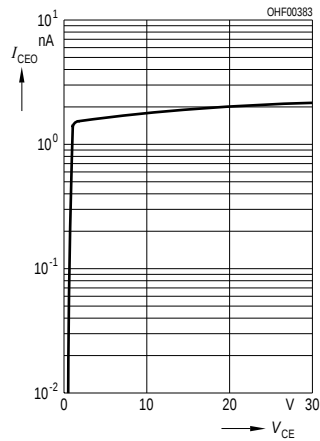


**Rel. Spectral Sensitivity,**  
 $S_{\text{rel}} = f(\lambda)$



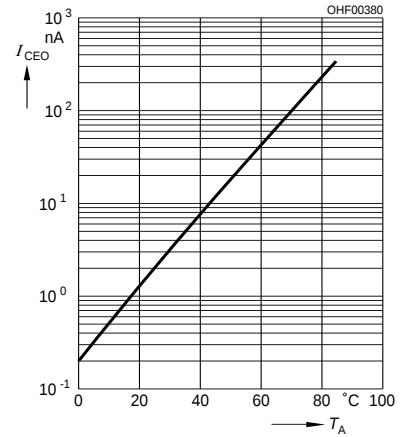
**Dark Current**

$$I_{\text{CEO}} = f(V_{\text{CE}}), E = 0$$

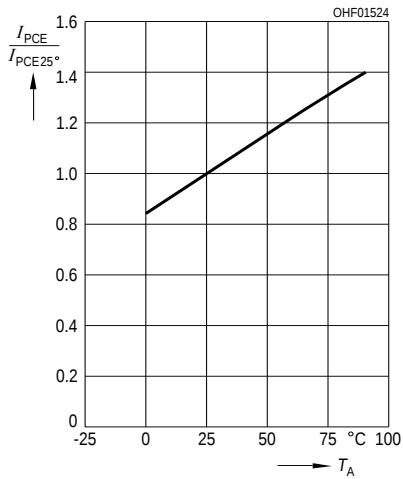


**Dark Current**

$$I_{\text{CEO}} = f(T_{\text{A}}), V_{\text{CE}} = 10 \text{ V}, E = 0$$

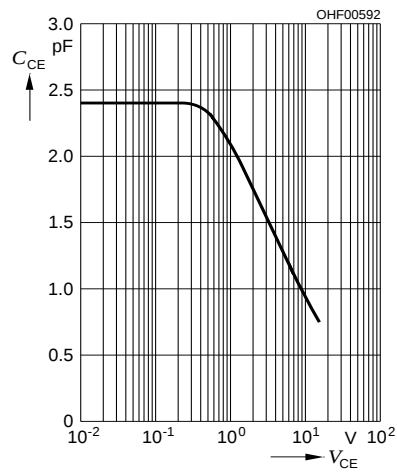


**Photocurrent  $I_{\text{PCE}} = f(T_{\text{A}})$ ,**  
 $V_{\text{CE}} = 5 \text{ V}$ , normalized to  $25^\circ\text{C}$

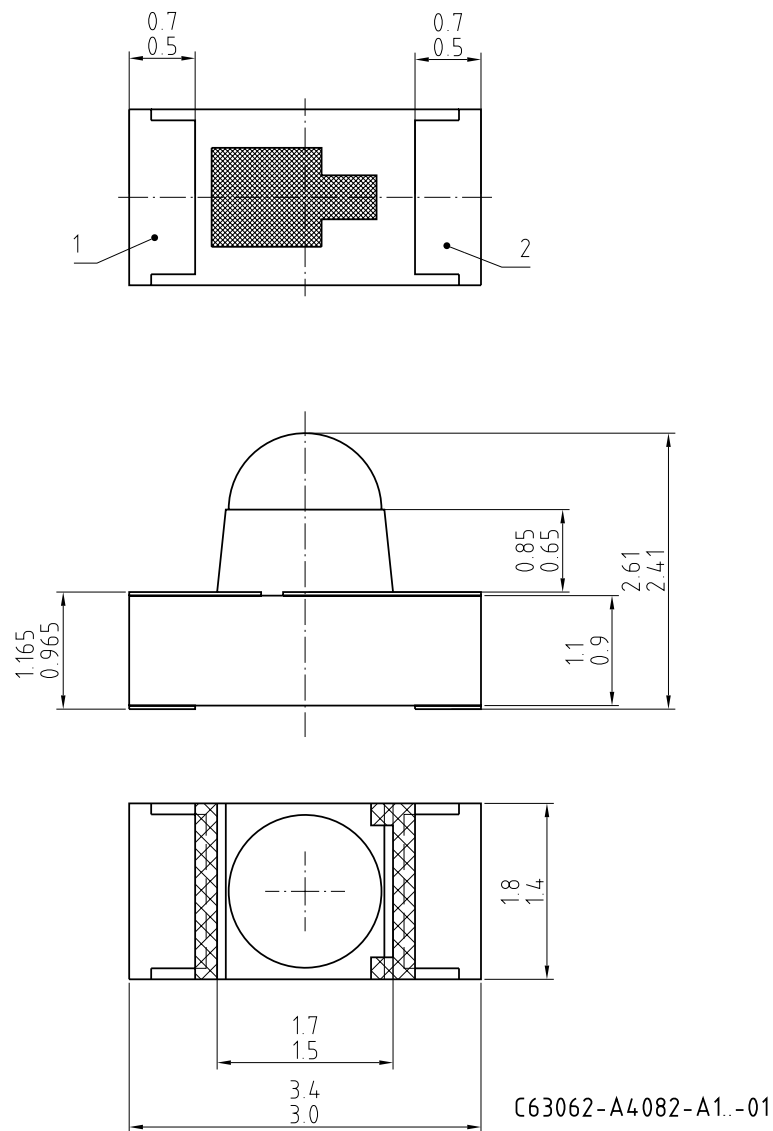


**Collector-Emitter Capacitance**

$$C_{\text{CE}} = f(V_{\text{CE}}), f = 1 \text{ MHz}$$

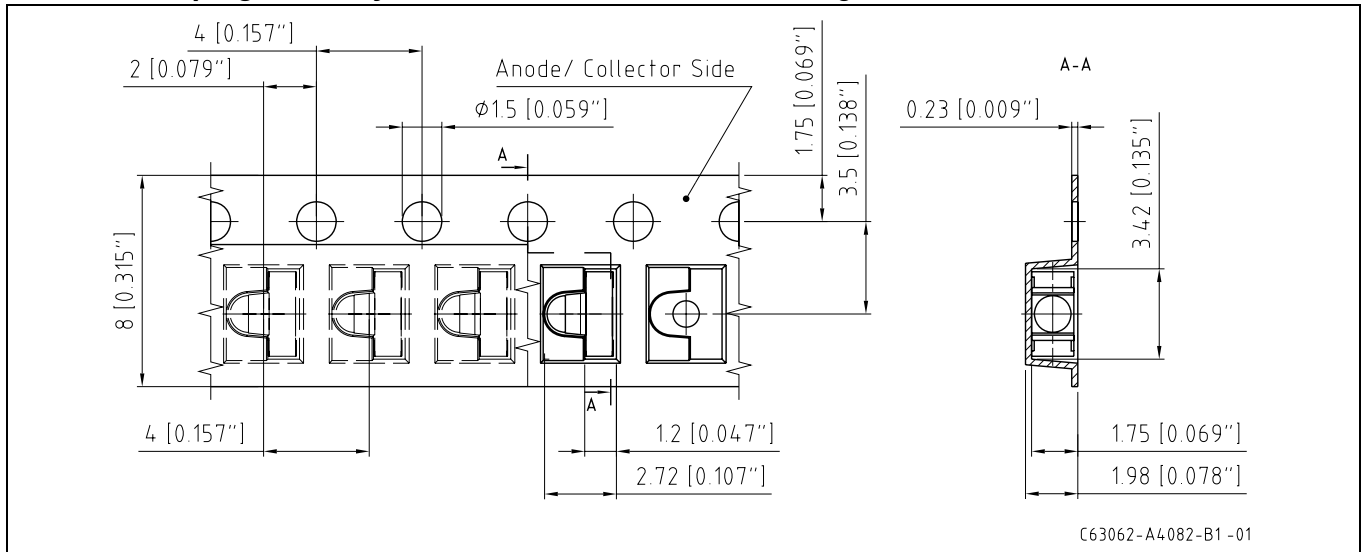


# **Maßzeichnung Package Outlines**



Maße in mm / Dimensions in mm.

|                                        |                                                    |
|----------------------------------------|----------------------------------------------------|
| Gehäuse / Package                      | Sidelooker mit Linse / Sidelooker with lens        |
| Anschlussbelegung<br>pin configuration | 1 = Emitter / emitter<br>2 = Kollektor / collector |
| Farbe<br>Color                         | schwarz<br>black                                   |

**Gurtung / Polarität und Lage**Verpackungseinheit 1500/Rolle,  $\varnothing 180$  mm**Method of Taping / Polarity and Orientation**Packing unit 1500/reel,  $\varnothing 180$  mm

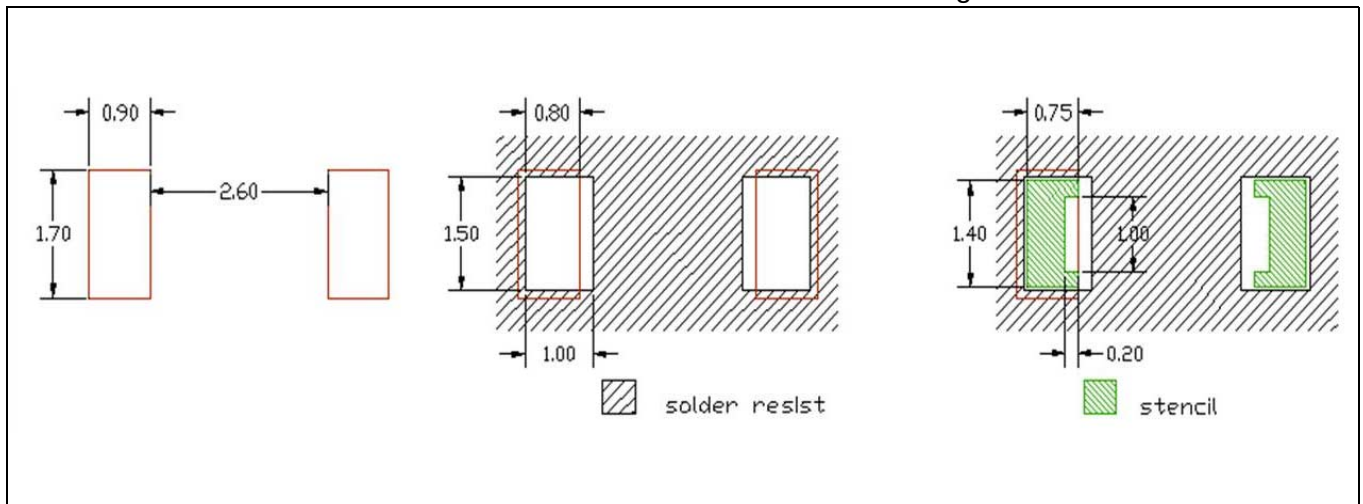
Maße in mm (inch) / Dimensions in mm (inch).

**Empfohlenes Lötpaddesign**

Reflow Lötén

**Recommended Solder Pad**

Reflow Soldering



Maße in mm / Dimensions in mm.

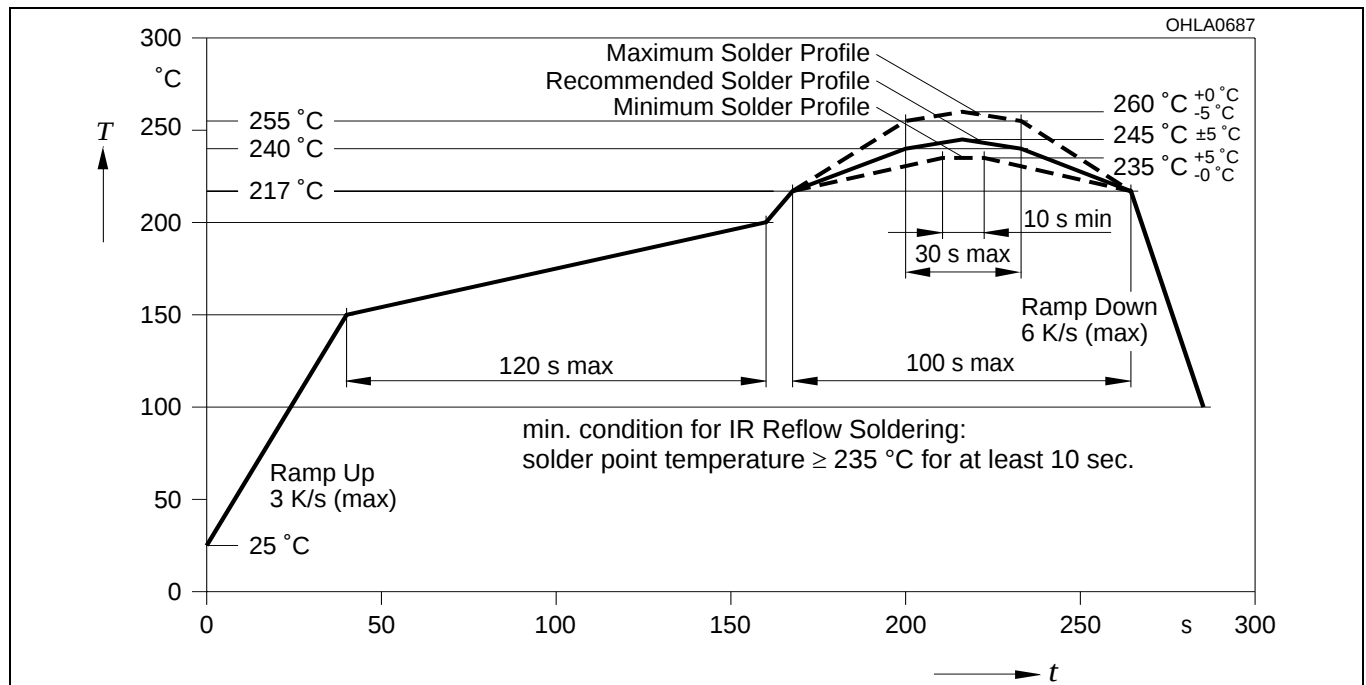
**Lötbedingungen****Soldering Conditions****Reflow Lötprofil für bleifreies Löt****Reflow Soldering Profile for lead free soldering**

Vorbehandlung nach JEDEC Level 3

Preconditioning acc. to JEDEC Level 3

(nach J-STD-020C)

(acc. to J-STD-020C)



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**Packing**

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

**Components used in life-support devices or systems must be expressly authorized for such purpose!** Critical components<sup>1</sup>, may only be used in life-support devices or systems<sup>2</sup> with the express written approval of OSRAM OS.

<sup>1</sup> A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

<sup>2</sup> Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered.

EU RoHS and China RoHS compliant product



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